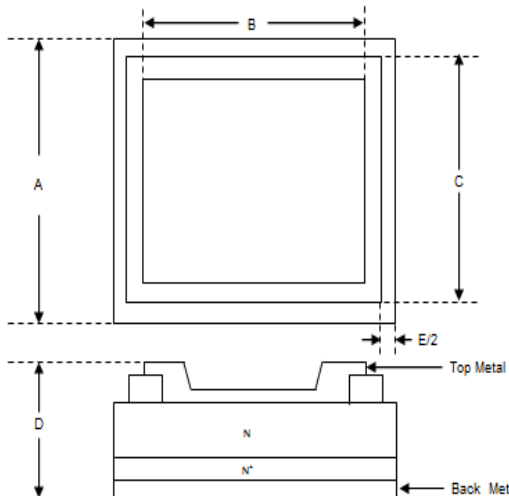


BM2200BG

200V, 20A⁽¹⁾, XTBR series Schottky

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2590 μm	102 mil
	Top Metal Pad Size (B)	2405 μm	94.7 mil
	Passivation Seal (C)	2510 μm	98.8 mil
	Wafer Thickness (D)	254±15 μm	10±0.6 mil
	Scribe Line Width (E)	80μm	3.15 mil
	Wafer Diameter	6 inch	
	Gross Die	2296	
	Top Side Metallization/ Layer Thickness	Ag / 3 ±0.3 μm	
	Back Side Metallization/ Layer Thickness	Ag / 2 ±0.2 μm	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

Electrical Characteristics in C/P test (T_J=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	200	—	—	V	I _R =300μA
V _F	Instantaneous Forward Voltage	—	0.69	0.72	V	I _F =3A ⁽²⁾
		—	0.825	0.90	V	I _F =10A ⁽²⁾
I _R	Reverse Leakage Current	—	6.5	12	μA	V _R =200V
T _J , T _{STG}	Operating and Storage Temperature	-40°C to 150°C Max				